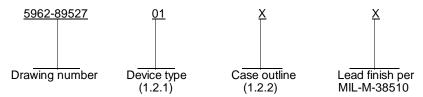
	1							R	REVISI	ONS			I							
LTR					Ε	DESCF	RIPTIO	N					DATE	E (YR-M	(O-DA			APPR	OVED)
A	Updated drawing to reference MIL-STD-1835. Made the changes to table I: output low voltage, changed I _{OL} from -1.6 mA; interrupt pulse width, PW _{IRQ} , changed units from t _{cyc} ; conversion time, changed max limit from t _{cyc} +32000; t _{cyc} +40000; delay time, t _{ASED} , changed min limit from 10,95.5. Modified figure 1, case outline Y. Editorial changes throughout.									e follow -1.6 m m ns to 0 to 05.5 to s	ing iA to i			92-1	2-04		Mon	ica L.	Poelkii	ng
REV																				<u> </u>
SHEET	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	A
SHEET	A 15	A 16	A 17	A 18	A 19	A 20	A 21	A 22	A 23	A 24	A 25	A 26	A 27	A 28	A 29	A 30	A 31	A 32	A 33	A 34
SHEET REV SHEET	15				19															
SHEET REV SHEET REV STATUS	15			18	19		21	22	23	24	25	26	27	28	29	30	31	32	33	34 A
SHEET REV SHEET REV STATUS OF SHEETS	15			18 REV SHE	19	20 Y	21 A	22 A	23 A	24 A 4	25 A 5	26 A 6	A 7	28 A 8	29 A 9	30 A	31 A 11	32 A 12	33 A	34 A
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STANE	15	16		18 REV SHE PREP, T	19 / ET ARED B	Y oh	21 A	22 A	23 A	24 A 4	25 A 5	26 A 6	A 7	28 A 8	29 A 9	30 A 10	31 A 11	32 A 12	33 A	34 A
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STANE MIL DR. THIS DRAWII FOR U	DARDI LITAR AWING NG IS A	IZED Y G	17	18 REV SHE PREP, T CHEC T	19 ARED B im H. No KED BY im H. No	Y oh	21 A 1	22 A	23 A	A 4 MICF CMO	25 A 5 DEFE	26 A 6	27 A 7 ELECT DA	28 A 8 RONIC	29 A 9 SS SU , OHIC	30 A 10 PPLY 0 4544	31 A 11	32 A 12	33 A	34 A
MIL DRAWII THIS DRAWII FOR U	DARDI LITAR AWIN NG IS A SE BY RTMEN NCIES	IZED Y G AVAILA ALL NTS OF TH	17 ABLE	18 REV SHE PREP, T CHEC T APPRO Will	19 ARED B im H. No KED BY im H. No OVED B	y y oh y Heckma	21 A 1	22 A 2	23 A	A 4 MICF CMO	25 A 5 DEFE	26 A 6 NSE E	27 A 7 ELECT DA	28 A 8 RONIC YTON AL, HIC	29 A 9 SS SU , OHIC	30 A 10 PPLY 0 4544 PEED	31 A 11 CENT 14	32 A 12	33 A 13	34

1. SCOPE

1.1 <u>Scope</u>. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".

1.2 Part or Identifying Number (PIN). The complete PIN shall be as shown in the following example:



1.2.1 <u>Device type(s)</u>. The device type(s) shall identify the circuit function as follows:

Device type	Generic number	Circuit function
01	68HC811E2	8-bit microcontroller, EEPROM 2K bytes, RAM 256 bytes

1.2.2 <u>Case outline(s)</u>. The case outline(s) shall be as designated in MIL-STD-1835, and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
X	GDIP1-T48 or CDIP2-T48	48	Dual-in-line
Y	See figure 1	52	Square leaded chip carrier

1.3 Absolute maximum ratings.

Supply voltage range	-0.3 V dc to +7.0 V dc
Storage temperature range	-65°C to +150°C
Maximum power dissipation (P _D)	1.75 W
Lead temperature (soldering, 5 seconds)	+270°C
Junction temperature (T _I)	+150°C
Thermal resistance, junction to case (Θ_{JC}) :	See MIL-STD-1835

1.4 Recommended operating conditions.

Supply voltage range (V _{DD})	4.5 V dc minimum to 5.5 V dc maximum
High level input voltage $(\nabla_{I \sqcup})$	0.8 x V _{DD}
Low level input voltage range (V _{II})	V _{SS} to 0.2 V dc x V _{DD} V _{DD} -0.1 V dc
Maximum high level output voltage (V _{OH})	V _{DD} -0.1 V dc
Maximum low level output voltage (VOL):	0.47 dc
Case operating temperature range (T _C)	-55°C to +125°C
Frequency of operation	DC to 2.1 MHz

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MICROCIRCUIT DRAWING
DEFENSE SUPPLY CENTER COLUMBUS
COLUMBUS, OHIO 43216-5000

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2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and bulletin</u>. Unless otherwise specified, the following specification, standard, and bulletin of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510 - Microcircuits, General Specification for.

STANDARDS

MILITARY

MIL-STD-481 - Configuration Control - Engineering Changes, (Short Form), Deviations and Waivers.

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

MIL-STD-1835 - Microcircuit Case Outlines.

BULLETIN

MILITARY

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

(Copies of the specification, standards, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
- 3.2.1 Case outline(s). The case outline(s) shall be as specified on figure 1 and in accordance with 1.2.2 herein.
- 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.
- 3.2.3 Block diagram. The block diagram shall be as specified on figure 3.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.
- 3.5 <u>Marking</u>. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103 (see 6.7 herein).
- 3.6 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7 herein). The certificate of compliance submitted to DESC-ECC prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change</u>. Notification of change to DESC-ECC shall be required in accordance with MIL-STD-883 (see 3.1 herein).

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	TABLE	I. <u>Electrica</u>	al performance characteri	stics.			
Test		Symbol	Conditions $\underline{1}/4.5 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $\text{V}_{SS} = 0 \text{ V} \text{ dc}$ $-55^{\circ} \text{ C} \le \text{T}_{\text{C}} \le +125^{\circ} \text{ C}$	Group A subgroups	<u>Limits</u> Min	Max	_ Unit
Output high voltage: All outputs except RESET, XTAL, and MODA		V _{OH}	I _{OH} = -0.8 mA V _{DD} = 4.5 V <u>1</u> /	1,2,3	V _{DD} -0.8		V
Output low voltage: All outputs except X	TAL	V _{OL}	I _{OL} = 1.6 mA V _{DD} = 4.5 V	1,2,3		0.4	V
Input high voltage	All inputs except RESET	V _{IH}		1,2,3	0.7 V _{DD}	V _{DD}	V
	RESET				0.8 V _{DD}	V _{DD}	
Input low voltage:	All inputs	V _{IL}		1,2,3	V _{SS}	0.2 V _{DD}	V
I/O ports, three-state leakage PA3, PA7, PC0-PC7, PD0-PD5, AS/STRA, MODA/LIR, RESET		l _{OZ}	$V_{IN} = V_{IH}$ or V_{IL}	1,2,3		±10	μА
Input current	PA0 - PA2, IRQ, XIRQ	I _{IN}	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{DD} = 5.5 \text{ V}$	1,2,3		±1	μΑ
_	MODB/V _{stby}		<u>2</u> /			±10	
RAM standby voltage	powerdown	V _{SB}		1,2,3	4.0	V _{DD}	V
RAM standby current	powerdown	I _{SB}		1,2,3		20	μA
Total supply current 3/	RUN:	I _{DD}	V _{DD} = 5.5 V Single chip V _{DD} = 5.5 V Expanded multiplexed	1,2,3		20	mA
G.	WAIT: All peripheral functions shut down	WI _{DD}	V _{DD} = 5.5 V Single-chip mode V _{DD} = 5.5 V Expanded multiplexed	1,2,3		10	_
	STOP: No clocks	SI _{DD}	V _{DD} = 5.5 V Single-chip mode			300	μΑ
Input capacitance	PA0-PA2, <u>PE0</u> -P <u>E7,</u> EXTAL, IRQ, XIRQ	C _{IN}	V _{IN} = 0 V f _{IN} = 1 MHz See 4.3.1c	4		8	pF
	PA7, PA3, PCO-PC7, PD0-P <u>D5,</u> A <u>SSTRA</u> MODA/LIR, RESET					14	
Functional tests			V _{DD} = 4.5 V, 5.5 V	7,8			
<u> </u>		-+	+	1			

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Test		Symbol	Conditions 1/	Group A	1.0 M	Hz	2.1 MF	łz	Unit
			4.5 V \leq V _{DD} \leq 5.5 V V _{SS} = 0 V dc -55 °C \leq T _C \leq +125 °C	subgroups	Min	Max	Min Max		
			Control timi	ng		•	'	.	
Frequenc	y of operation	f _o	See figure 4	9,10,11	0	1.0	0	2.1	MHz
E clock pe	eriod	t _{cyc}		9,10,11	1000.0		476.0		ns
Crystal fre	equency	f _{XTAL}		9,10,11		4.0		8.4	MHz
External o		f _{oEX}		9,10,11	0	4.0	0	8.4	MHz
Processo	r control setup	t _{PCS}		9,10,11	200.0		69.0		ns
Reset input pulse width	To guarantee external reset vector 4/	PW _{RSTL}		9,10,11	8.0		8.0		t _{cyc}
	Minimum input time may be preempted by internal reset			9,10,11	1.0		1.0		
Mode pro time	gramming setup	t _{MPS}		9,10,11	2.0		2.0		t _{cyc}
Mode pro time	gramming hold	t _{MPH}	_	9,10,11	0.0		0.0		ns
I <u>nter</u> rupt p IRQ edg mode	oulse width e sensitive	PW _{IRQ}	_	9,10,11	2.0		2.0		t _{cyc}
Wait reco time	very startup	t _{WRS}		9,10,11		4.0		4.0	t _{cyc}
Timer puls	se width oture, pulse ator input	PW _{TIM}		9,10,11	1020.0		496.0		ns

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		TAI	BLE I. <u>Electrical performance chara</u>	cteristics - Co	ontinued.				
Test		Symbol	I Conditions 1/	Group A	1.0 MHz		2.1 MHz		Unit
			4.5 V ≤ V _{DD} ≤ 5.5 V V _{SS} = 0 V dc -55° C ≤ T _C ≤ +125° C	subgroups	Min	Max	Min	Max	
			Peripheral port timing	<u>5</u> /		•			
Frequency of (E clock freq		f _o	See figure 4	9,10,11	1.0	1.0	2.1	2.1	MHz
E clock period	I	t _{cyc}		9,10,11	1000.0		476.0		ns
Peripheral dat time MCU re ports A, C, D	ad of ·	t _{PDSU}		9,10,11	100.0		100.0		ns
Peripheral dat time MCU re A, C, D, and	ad of ports	t _{PDH}		9,10,11	50.0		50.0		ns
Delay time, peripheral	MCU write to port A	t _{PWD}		9,10,11		175		175	ns
data write	MCU write to port B, C, and D					340.0		209.0	
Input data set	up time	t _{IS}		9,10,11	60.0		60.0		ns
Input data hole (port C)	d time	t _{IH}		9,10,11	100.0		100.0		ns
Delay time, En	fall	t _{DEB}		9,10,11		350.0		219.0	ns
Setup time, Sasserted to E	TRA E fall <u>6</u> /	t _{AES}		9,10,11	0.0		0.0		ns
Delay time, ST asserted to p	ort C,	t _{PCD}		9,10,11		100.0		100.0	ns
Hold time, ST to port C data	RA negated a	t _{PCH}		9,10,11	10.0		10.0		ns
Three-state ho	old time	t _{PCZ}		9,10,11		150.0		150.0	ns

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		BLE I. Electrical performance characte				
Test	Symbol	$ \begin{array}{c} Conditions \\ 4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} \\ \text{V}_{SS} = 0 \text{ V dc} \\ -55^{\circ} \text{ C} \leq \text{T}_{C} \leq 125^{\circ} \text{ C} \\ 750 \text{ kHz} \leq \text{E} \leq 2.1 \text{ MHz} \\ \end{array} $	Group A subgroups	Limits Min Max		Unit
		A/D converter				
Resolution	RES	Number of bits resolved by the A/D	4,5,6	8		Bits
Non-linearity	NLI	Maximum deviation from the ideal and A/D transfer characteristics	4,5,6		±0.5	LSB
Zero error	ZER	Difference between the output of an ideal and an actual A/D for zero input voltage	4,5,6		±0.5	LSB
Full-scale error	FSE	Difference between the output of an ideal and an actual A/D for full-scale input voltage	4,5,6		±0.5	LSE
Total unadjusted error	TUE	Maximum sum of non-linearity, zero error, and full-scale error	4,5,6		±0.5	LSB
Quantization error	QTE	Uncertainty due to converter resolution	4,5,6		±0.5	LSE
Absolute accuracy	AAC	Difference between the actual input voltage and the full-scale weighted equivalent of the binary output code, all error sources included	4,5,6		±1	LSE
Conversion range	COR	Analog input voltage range	4,5,6	V _{RL}	V _{RH}	V
Maximum analog reference voltage	V _{RH}	7/	4,5,6	V _{RL}	V _{DD} +0.1	V
Minimum analog reference voltage	V_{RL}	Z/	4,5,6	V _{SS} -0.1	V _{RH}	V

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		TABL	E I. Electrical perfo	ormance characteristic	s - Continued.			
Test		Symbol	Conditions		Group A	Limits		Unit
			$\begin{array}{c} 4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} \\ \text{V}_{SS} = 0 \text{ V} \text{ dc} \\ \text{-55}^{\circ}\text{C} \leq \text{T}_{C} \leq +125^{\circ}\text{C} \\ 750 \text{ kHz} \leq \text{E} \leq 2.1 \text{ MHz} \end{array}$		subgroups	Min	Max	
Minimum diffe	erence between L	Delta V _R	7/		4,5,6	3		V
Conversion	E clock	CONT	Total time to perfo	Total time to perform a single			32 <u>8</u> /	t _{cyc}
time	Internal RC oscillator <u>8</u> /		analog-to-digital conversion				t _{cyc} +40000	ns
Monotonicity		MON	Conversion result never 9/decreases with an increase in input voltage and has no missing codes		4,5,6			
Zero input rea	ading	ZIR	Conversion result $V_{IN} = V_{RL}$	when	4,5,6	0.0		Hex
Full scale read	ding	FSR	Conversion result $V_{IN} = V_{RH}$	when	4,5,6		FF	Hex
Sample acqui	sition time	SAT	Analog input acquisition	E clock	4,5,6	12		t _{cyc}
			sampling time	Internal RC 11/ oscillator			12	μs
Input leakage I _{IN} Input leakage		Input leakage	PE0-PE7			400	nA	
			on A/D pins	V_{RL}, V_{RH}	9,10,11		1.0	μΑ

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	IAL	BLE I. Electrical performance c			·•			
Test Symbo	Symbol	Conditions 1	Group A	1.0 MH	lz	2.1 MHz		Unit
		4.5 V ≤ V _{DD} ≤ 5.5 V V _{SS} = 0 V dc -55° C ≤ T _C ≤ +125° C	subgroups	Min	Max	Min	Max	
		Expansion bus timing						
Frequency of operation (E clock frequency)	f _o	V _{DD} = 4.5 V See figure 4	9,10,11	1.0	1.0	2.1	2.1	MH
Cycle time	t _{cyc}		9,10,11	1000.0		476.0		ns
Pulse width, E low	PW _{EL}		9,10,11	477.0		215.0		ns
Pulse width, E high	PW _{EH}		9,10,11	472.0		210.0		ns
E and AS rise time	t _r		9,10,11		20.0		20.0	ns
E and AS fall time	t _f		9,10,11		20.0		20.0	ns
Address hold time	t _{AH}		9,10,11	95.5		30.0		ns
Non-muxed address valid time to E rise 9/	t _{AV}		9,10,11	281.5		85.0		ns
Read data setup time	t _{DSR}		9,10,11	30.0		30.0		ns
Read data hold time	^t DHR		9,10,11	10.0	145.5	10.0	80.0	ns
Write data delay time <u>8a</u> /	t _{DDW}		9,10,11		190.5		125.0	ns
Write data hold time 8a/	t _{DHW}		9,10,11	95.5		30.0		ns
Muxed address valid time to E rise 8b/	t _{AVM}		9,10,11	271.5		75.0		ns

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	TAI	BLE I. Electrical performance cha	aracteristics -	Continued	l.			
Test	Symbol	Conditions	Group A	1.0 MHz		2.1 MHz		Unit
		$4.5 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $\text{V}_{SS} = 0 \text{ V dc}$ $-55^{\circ}\text{ C} \le \text{T}_{C} \le +125^{\circ}\text{ C}$	subgroups	Min	Max	Min	Max	
Muxed address valid time to AS fall	t _{ASL}	V _{DD} = 4.5 V See figure 4	9,10,11	151.0		20.0		ns
Muxed address hold time 8b/	t _{AHL}		9,10,11	95.5		30.0		ns
Delay time, E to AS rise 8b/	t _{ASD}		9,10,11	115.5		50.0		ns
Pulse width, AS high	PW _{ASH}		9,10,11	221.0		90.0		ns
Delay time, AS to E rise 8b/	t _{ASED}		9,10,11	95.5		40.0		ns
MPU address access time 8b/	t _{ACCA}		9,10,11	733.5		275.0		ns
MPU access time	t _{ACCE}		9,10,11		442.0		180.0	ns
Muxed address delay (previous cycle MPU read) <u>8a</u> /	t _{MAD}		9,10,11	145.5		80.0		ns

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Test		Symbol	Conditions	Group A	Limits		Unit
			$\begin{array}{c} 4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} \\ \text{V}_{SS} = 0 \text{ V dc} \\ \text{-55}^{\circ}\text{C} \leq \text{T}_{C} \leq \text{+125}^{\circ}\text{C} \end{array}$	subgroups	Min	Max	
			Serial peripheral interface (SPI) tim	ing		1	
Operating frequency	Master slave	f _{op(m)} f _{op(s)}	V _{DD} = 4.5 V See figure 4	9,10,11 9,10,11	0	0.5 2.1	MHz
Cycle time	Master slave	t _{cyc(m)}		9,10,11	2.0		t _{cyc}
-		t _{cyc(s)}		9,10,11	480		ns
Enable lead time	Master slave	tlead(m) tlead(s)		9,10,11 9,10,11	<u>12</u> / 240		ns
Enable lag time	Master slave	t _{lag(m)}		9,10,11 9,10,11	<u>12</u> / 240		ns
Clock (SCK) high time	Master slave	tw(SCKH)mtw(SCKH)s		9,10,11 9,10,11	340 190		ns
Clock (SCK) low time	Master slave	tw(SCKL)m tw(SCKL)s		9,10,11 9,10,11	340 190		ns
Data setup time	Master slave	t _{su(m)} t _{su(s)}		9,10,11 9,10,11	100 100		ns
Data hold time	Master slave	th(m) th(s)		9,10,11 9,10,11	100 100		ns
Access time (time to data from high impedance s	a active tate) slave	t _a		9,10,11	0	120	ns
Disable time (hold time to impedance state) slave	o high-	t _{dis}		9,10,11		240	ns
Data valid (after enable e	edge) <u>13</u> /	t _{V(S)}		9,10,11		240	ns
Data hold time (outputs, after enable e	-dge)	t _{ho}		9,10,11	0		ns

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TABLE I. <u>Electrical performance characteristics</u> - Continued.								
5	Symbol	Conditions 4.5 V ≤ V _{DD} ≤ 5.5 V	Group A subgroups	<u>Lir</u> Min				

Т	Test		Symbol	Condition	S	Group A	Limits		Unit
				4.5 V ≤ V _{DD} ≤ 5.5 V V _{SS} = 0 V dc -55° C ≤ T _C ≤ +125° C		subgroups	Min	Max	
Rise time	SCK, MOSI, and MISO		t _{rm}	V _{DD} = 4.5 V See figure 4	20% V _{DD} to 70% V _{DD} C _L = 200 pF	9,10,11		100	ns
- I	SCK	\overline{S} , MOSI, MISO, and \overline{SS}	t _{rs}	C	C _L = 200 pF	9,10,11		2.0	μs
Fall time	SCK	X, MOSI, and MISO	t _{fm}		70% V _{DD} to 20% V _{DD}	9,10,11		100	ns
-	SCK, MOSI, MISO, and \overline{SS}		t _{fs}		C _L = 200 pF	9,10,11		2.0	μs
Programm time	ning	14/ 2.1 MHz RC oscillator 15/ enabled		V _{DD} = 4.5 V Not shown	,	9,10,11	<u>25</u> 25		ms
Erase time	e	Byte, row, and bulk		_		9,10,11	25		ms
Write/erase endurance			+			5,000		cycles	
Data reter	Data retention 16/						10		years

V_{OH} specification for RESET and MODA is not applicable because they are open-drain pins. V_{OH} specification not applicable to ports C and D in wire-OR mode. See A/D specification for leakage current for port E.

- All ports configured as inputs, $V_{IL} \le 0.2 \text{ V}$, $V_{IH} \ge V_{DD}$ -0.2 V, no dc loads, EXTAL driven with a square wave, <u>3</u>/ and t_{cyc} = 476.5 ns.

 RESET will be recognized during the first clock cycle it is held low. Internal circuitry then drives the pin low
- for four clock cycles, releases the pin, and samples the pin level two cycles later to determine the source of the interrupt.
- Ports C and D timing is valid for active drive (CWOM and DWOM bits not set in PIOC and SPCR registers respectively).
- If this setup time is met, STRB will acknowledge in the next cycle. If it is not met, the response may be delayed one more cycle.

Performance verified down to 2.5 V ΔV_R , but accuracy is tested and guaranteed at ΔV_R = 5 V \pm 10 percent. Source impedances greater than 10 k Ω will adversely affect accuracy, due mainly to input leakage. 7/

Input clocks with duty cycles other than 50 percent will affect bus performance. Timing parameters affected by input clock duty cycle are identified by "a" and "b". To recalculate the approximate bus timing values, substitute the following expressions in place of 1/8 $t_{
m cyc}$ in the above formulas where applicable:

a. (1-dc) x (1/4 x t_{cyc})

- b. DC x $(1/4 \times t_{cyc})^{yc}$ Where dc is the decimal value of duty cycle percentage (high time).
- Subgroups 4, 5, and 6 shall be guaranteed for all bits.

Absolute (shall be exact value).

- Conversions using internal RC oscillator not tested at -55°C.
- Signal production depends on software.
- Assumes 200 pF load on all SPI pins.
- Programming time tested at 2.1 MHz with internal RC oscillator disabled for all three temperatures. <u>14</u>/
- Programming time with internal RC oscillator enabled is tested at 500 kHz. Recommend that internal RC oscillator be used when frequency falls below 1.0 MHz or when temperature exceeds 85°C and frequency falls below 2.0 MHz.
- The 10 years specified is based on an average operating temperature of 70°C.

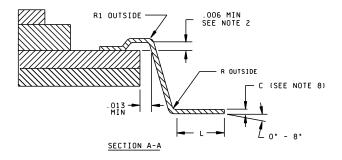
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	12

Case outline Y INDEX AND PIN NO 1 ID AREA (SEE NOTES 1 AND 4) - нD e 1 4 PLACES – A – ΗE N-4 PLACES e b N-PLACES SEE NOTE 8 .012 M C A S B S .004 (M) C — B — - C -SEATING PLANE

FIGURE 1. Case outlines.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	13

Case outline Y



Case Y					
	Inch	es	Millir	neters	
Symbol	Min	Max	Min	Max	
А		.125		3.175	
A1	.018	.035	0.457	0.889	
b	.018	.030	0.457	0.762	
С	.005	.010	0.127	0.254	
D/E	.940	.960	23.88	24.38	
е	.050 E	BSC			
e1	.800 E	BSC			
HD/HE	1.133	1.147	28.78	29.13	
L	.024	.040	0.610	1.016	
N	68		(68	
R	.011	.034	0.279	0.864	
R1	.009		0.229		

- 1. A terminal 1 identification mark shall be located at the index corner in the shaded area shown. Terminal 1 is located immediately adjacent to and counterclockwise from the index corner. Terminal numbers increase in a counterclockwise direction when viewed as shown.
- 2. Generic lead attach dogleg depiction.
- 3. Dimension N: Number of terminals.
- 4. Corner shapes (square, notch, radius, etc.) may vary from that shown on the drawing. The index corner shall be clearly unique.
- 5. Metric equivalents are given for general information only.
- 6. Controlling dimension: Inch.
- 7. Datums X and Y to be determined where center leads exit the body.
- 8. Dimensions b and c include lead finish.

FIGURE 1. Case outlines - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	14

Device type	01					
Case outline		Х				
Terminal	Terminal	Terminal	Terminal			
number	symbol	number	symbol			
1	PA7/PAI/OC1	25	MODA/ LTR			
2	PA6/OC2/OC1	26	STRA/AS			
3	PA5/OC3/OC1	27	E			
4	PA4/OC4/OC1	28	STRB/R/W			
5	PA3/OC5/OC1	29	EXTAL			
6	PA2/IC1	30	XTAL			
7	PA1/IC2	31	PCO/ADO			
8	PA0/IC3	32	PC1/AD1			
9	PB7/A15	33	PC2/AD2			
10	PB6/A14	34	PC3/AD3			
11	PB5/A13	35	PC4/AD4			
12	PB4/A12	36	PC5/AD5			
13	PB3/A11	37	PC6/AD6			
14	PB2/A10	38	PC7/AD7			
15	PB1/A9	39	RESET			
16	PB0/A8	40	XTRQ			
17	PE0/AN0	41	TRQ			
18	PE1/AN1	42	PDO/RXD			
19	PE2/AN2	43	PD1/txD			
20	PE3/AN3	44	PD2/MISO			
21	VRL	45	PD3/MOSI			
22	VRH	46	PD4/SCK			
23	VSS	47	PD5/SS			
24	MODB/V _{stby}	48	VDD			

FIGURE 2. <u>Terminal connections</u>

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	15

Device type	01					
Case outline		Υ				
Terminal number			Terminal symbol			
1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26	XTAL PC0/AD0 PC1/AD1 PC2/AD2 PC3/AD3 PC4/AD4 PC5/AD5 PC6/AD6 PC7/AD7 RESET X1RQ 1RQ PD0/RxD PD1/TxD PD2/MISO PD3/MOSI PD4/SCK PD5/SS VDD PA7/PAI/OC1 PA6/OC2/OC1 PA6/OC3/OC1 PA4/OC4/OC1 PA3/OC5/OC1 PA1/IC2	27 28 29 30 31 32 33 34 35 36 37 38 39 40 41 42 43 44 45 46 47 48 49 50 51 52	PA0/IC3 PB7/A15 PB6/A14 PB5/A13 PB4/A12 PB3/A11 PB2/A10 PB1/A9 PB0/A8 PE0/AN0 PE4/AN4 PE1/AN1 PE5/AN5 PE2/AN2 PE6/AN6 PE3/AN3 PE7/AN7 VRL VRH VSS MODB/V stby MODA/L1R STRA/AS E STRB/R/W EXTAL			

FIGURE 2. <u>Terminal connections</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	16

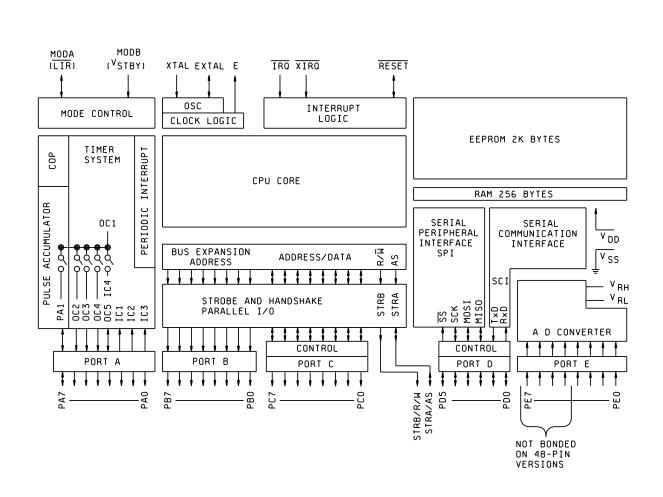
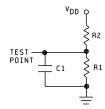


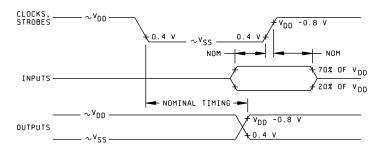
FIGURE 3. Block diagram.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	17

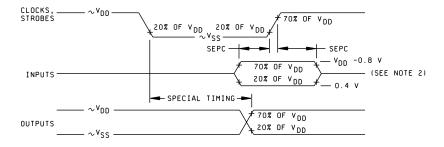
Equivalent test load

Pins	R1	R2	C1
PA3-PA7 PB0-PB7 PC0-PC7 PD0-PD6 E, AS, R/W	3.26 k	2.38 k	90 pF
PD1-PD4	3.26 k	2.38 k	200 pF





DC testing



AC testing

- Full test loads are applied during all ac electrical test and ac timing measurements.
 During ac timing measurements, inputs are driven to 0.4 volt and V_{DD} -0.8 volt while timing measurements are taken at the 20 percent and 70 percent of V_{DD} points.

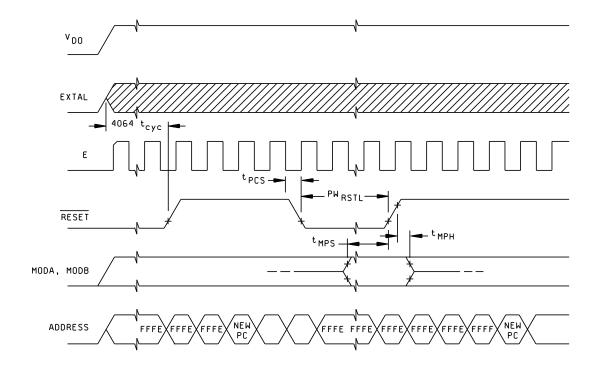
FIGURE 4. Test circuit and waveforms.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	18

PAO-PA2 SEE NOTE 1 PAO-PA2 SEE NOTE 2 PA7 SEE NOTE 1,3 PWTIMPA7 SEE NOTE 2,3

Timer inputs timing

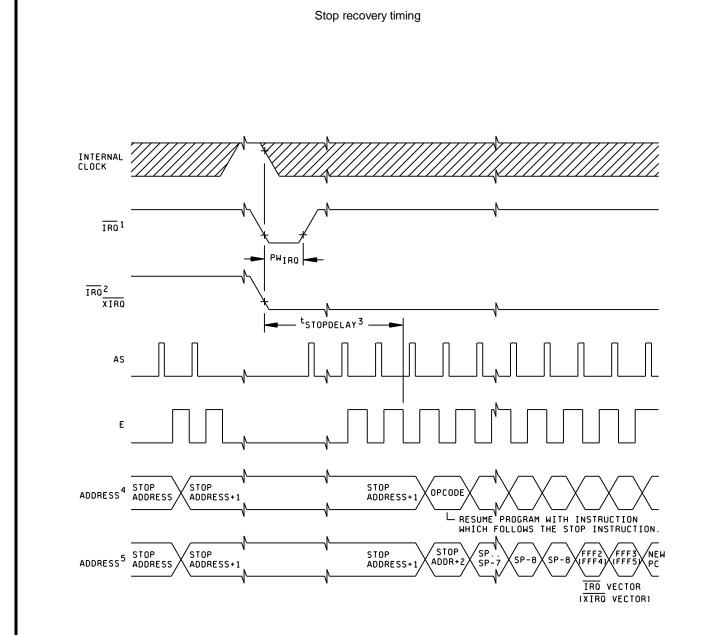
POR external reset timing



- Rising edge sensitive input.
 Falling edge sensitive input.
 Maximum pulse accumulator clocking rate is E frequency divided by 2.

FIGURE 4. Test circuit and waveforms - Continued.

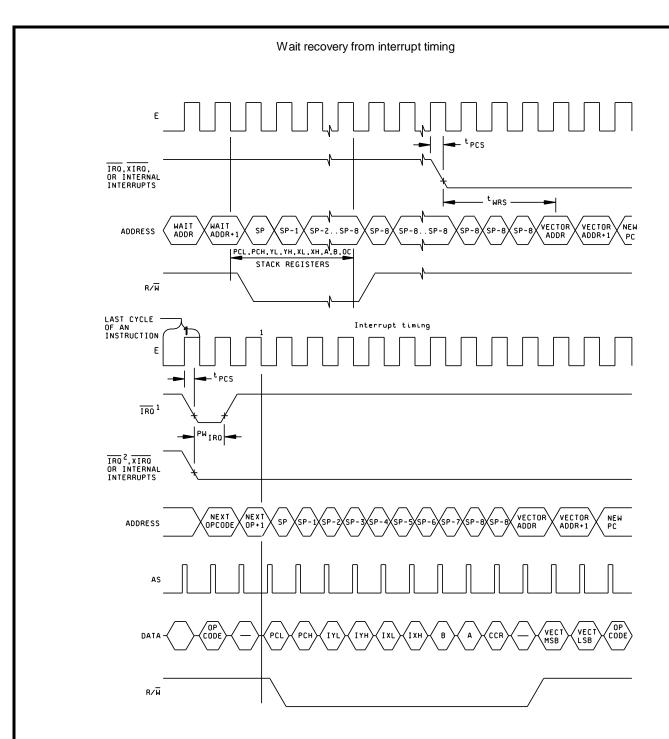
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	19



- 1. Edge sensitive <u>IRQ</u>pin (IRQE bit = 1).
 2. Level sensitive IRQ pin (IRQE bit = 0).
 3. t_{STOPDELAY} = 4064 t_{cyc} if DLY bit = 1 or 4 t_{cyc} if DLY = 0.
 4. <u>XIQ</u> with X bit in CCR = 1.
 5. IRQ or XIRQ with X bit in CCR = 0.

FIGURE 4. Test circuit and waveforms - Continued.

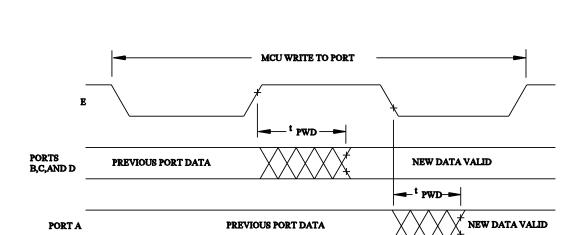
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL A	SHEET 20



- Edge sensitive <u>IRQ</u>pin (IRQE bit = 1).
 Level sensitive <u>IRQ</u> pin (IRQE bit = 0).

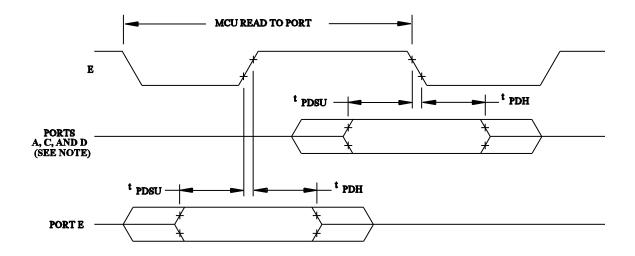
FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	21



Port write timing

Port read timing



NOTE: For nonlatched operation of port C.

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	22

PORT B PREVIOUS PORT DATA NEW DATA VALID **DEB** **STRB (OUT)

Simple output strobe timing

Simple input strobe timing

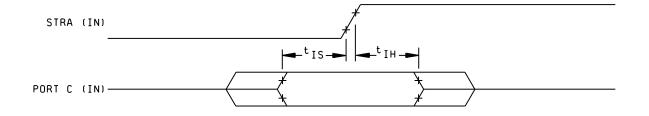
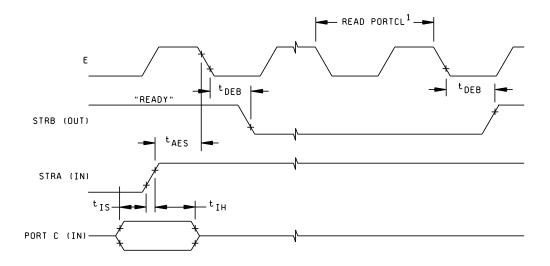


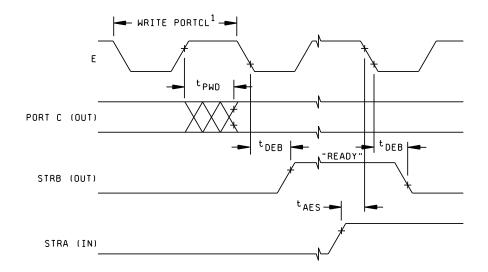
FIGURE 4. <u>Test circuit and waveforms</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL A	SHEET 23

Port C input handshake timing



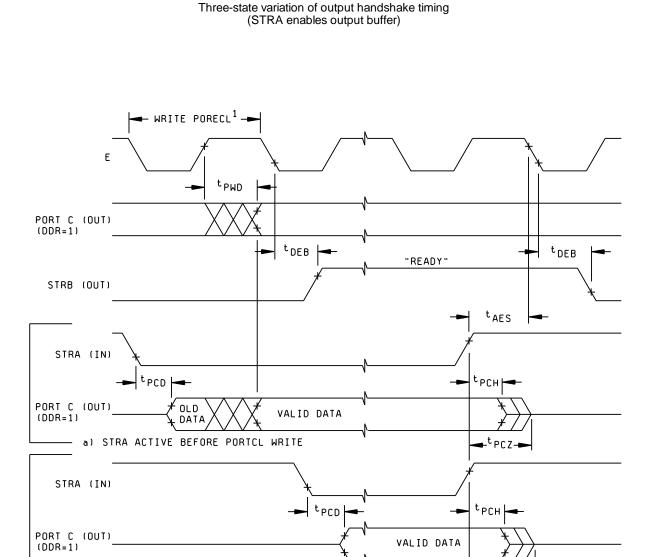
Port C output handshake timing



- After reading PIOC with STAF set.
 Figures show rising edge STRA (EGA = 1) and high true STRB (INVB = 1).

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	24



NOTES:

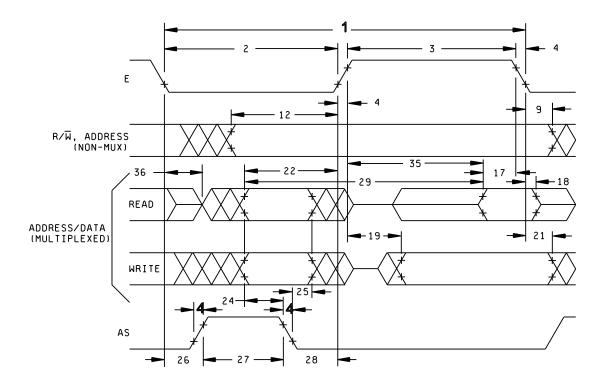
- After reading PIOC with STAF set.
 Figures show rising edge STRA (EGA = 1) and high true STRB (INVB = 1).

— b) STRA ACTIVE AFTER PORTCL WRITE

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	25

Expansion bus timing



NOTE: Measurement points shown are 20 percent and 70 percent V_{DD} .

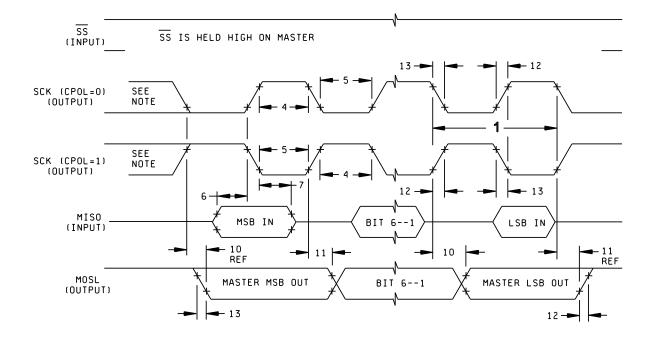
Waveform number references.

Number	Symbol	Number	Symbol	Number	Symbol	Number	Symbol
1	t _{cyc}	2	PW _{EL}	3	PW _{EH}	4	t _r , t _f
9	t _{AH}	12	t _{AV}	17	t _{DSR}	18	t _{DHR}
19	t _{DDW}	21	t _{DHW}	22	t _{AVM}	24	t _{ASL}
25	t _{AHL}	26	t _{ASD}	27	PW _{ASH}	28	t _{ASED}
29	t _{ACCA}	35	^t ACCE	36	t _{MAD}		

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	26



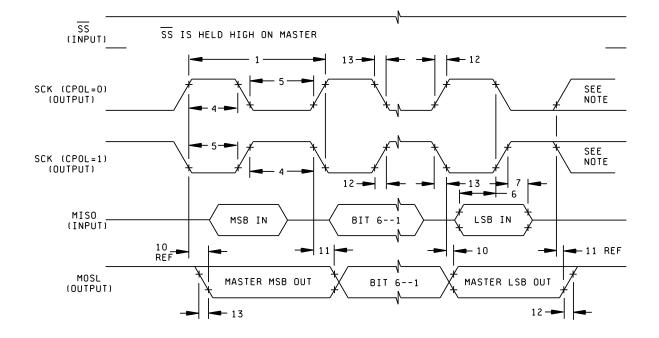


NOTE: This first clock edge is generated internally but is not seen at the SCK pin. SPI MASTER TIMING (CPHA = 0).

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL A	SHEET 27



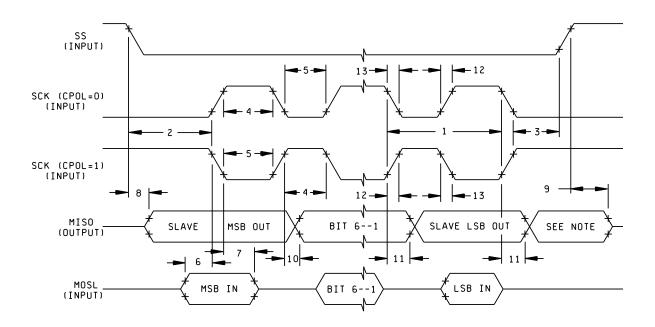


NOTE: This last clock edge is generated internally but is not seen at the SCK pin. SPI MASTER TIMING (CPHA = 0).

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	28

SPI timing

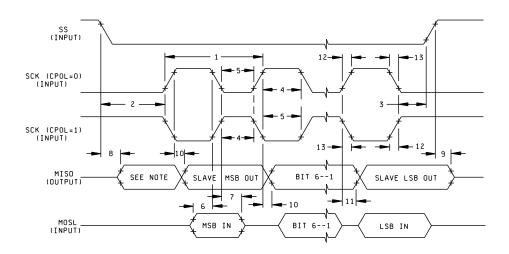


NOTE:Not defined but normally MSB of character just received. SPI SLAVE TIMING (CPHA = 0).

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	29

SPI timing



NOTE:Not defined but normally LSB of character previously transmitted. SPI SLAVE TIMING (CPHA = 0).

Waveform number references - SPI timing.

Number	Symbol	Master/slave	Number	Symbol	Master/slave
1	t _{cyc}	m,s	2	t _{lead}	m,s
3	t _{lag}	m,s	4	t _{w(SCKH)}	m,s
5	t _{w(SCKL)}	m,s	6	t _{su}	m,s
7	t _h	m,s	8	t _a	
9	t _{dis}		10	t _V	s
11	t _{ho}		12	t _r	m,s
13	t _f	m,s			

FIGURE 4. Test circuit and waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-89527
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		A	30

- 3.9 Verification and review. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 Processing EEPROMS. All testing requirements and quality assurance provisions herein shall be satisfied by the manufacturer prior to delivery.
- 3.10.1 Erasure of EEPROM. When specified, devices shall be erased in accordance with the procedures and characteristics specified in 4.4.
- 3.10.2 Programmability of EEPROM. When specified, devices shall be programmed to the specified pattern using the procedures and characteristics specified in 4.5.
- 3.10.3 Verification of erasure or programmability of EEPROM. When specified, devices shall be verified as either programmed to the specified pattern or erased. As a minimum, verification shall consist of performing a functional test (subgroup 7) to verify that all bits are in the proper state. Any bit that does not verify to be in the proper state shall constitute a device failure, and shall be removed from the lot.
 - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 Screening. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
 - Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - (2) $T_{\Delta} = +125^{\circ} \text{C}$, minimum.
 - Interim and final electrical test parameters shall be as specified in table II herein, except interim b. electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
 - An endurance/data retention test prior to burn-in, in accordance with method 1033 of MIL-STD-883, shall be C. included as part of the screening procedure with the following conditions:
 - (1) Cycling may be block, byte, or page at +125° C and shall cycle all bytes for a minimum of 1000 cycles and the devices shall remain at +125°C for 24 hours.
 - (2) After cycling, perform a high temperature unbiased bake for 72 hours at 150°C (minimum). The storage time may be accelerated by using higher temperature in accordance with the Arrhenius Relationship:

 $A_F = \exp(-E_A/K^*(1/T1 - 1/T2))$ where:

 $A_F =$ acceleration fac tor (unitless quantity) = t_1/t_2

T = temperature in Kelvin

 $t_1 = time$ (hrs) at temperature T1

 $t_2^{'}$ = time (hrs) K = Boltzmanns constant = 8.62 x 10⁻⁵ eV/° K using an apparent activation energy (E_A) of 0.6 V.

The maximum storage temperature shall not exceed 200°C for packaged devices or 300°C for unassembled devices.

Read the data retention pattern and test using subgroups 1, 7, and 9 (minimum, e.g., high temperature equivalent subgroups 2, 8A, and 10 may be used) after cycling and bake, prior to burn-in. Devices having bits not in the proper state after storage shall constitute a device failure.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE A		5962-89527
		REVISION LEVEL A	SHEET 31

4.3 <u>Quality conformance inspection</u>. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

4.3.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- Subgroup 4 (C_{IN} measurement) shall be measured only for the initial test and after process or design changes which may affect input capacitance. A minimum sample size of five devices with zero rejects shall be required.
- All devices selected for testing shall have the EEPROM programmed with a checkerboard pattern or equivalent.
 After completion of all testing, the devices shall be erased and verified (except devices submitted for groups C and D testing).
- d. Subgroups 7 and 8 shall consist of verifying the EEPROM pattern specified and the instruction set. The instruction set forms a part of the vendors test tape and shall be maintained and available from the approved source of supply upon request.

4.3.2 Groups C and D inspections.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. All devices requiring end-point electrical testing shall be programmed with a checkerboard or equivalent alternating bit pattern.
- c. Steady-state life test conditions, method 1005 of MIL-STD-883.
 - (1) Test condition A or D using the circuit submitted with the certificate of compliance (see 3.6 herein).
 - (2) $T_A = +125^{\circ} C$, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- d. An endurance test, in accordance with method 1033 of MIL-STD-883, shall be added to group C1 inspection prior to performing the steady-state life test (see 4.3.2c) and extended data retention (see 4.3.2e).

Cycling may be block, byte, or page from devices passing group A after the completion of the requirements of 4.2 herein

- (1) All bytes shall be cycled for a minimum of 4,000 cycles at +25° C.
- (2) Perform group A subgroups 1 and 7.
- e. Extended data retention shall consist of:
 - (1) All devices shall be programmed with a charge on all memory cells in each device, such that the cell will read opposite the state that the cell would read in its equilibrium state (e.g., worst case pattern, see 4.2c(2)).
 - (2) Perform a high temperature unbiased bake for 1000 hours at 150°C (minimum). The storage time may be accelerated by using higher temperature in accordance with the Arrhenius Relationship:

$$A_F = \exp(-E_A/K^*(1/T1 - 1/T2))$$
 where:

 A_F = acceleration factor (unitless quantity) = t_1/t_2

T'= temperature in Kelvin

 $t_1 = time$ (hrs) at temperature T1

 t_2 = time (hrs) at temperature T2

 $K = Boltzmanns constant = 8.62 \times 10^{-5} eV/^{\circ} K$ using an apparent activation energy (E_A) of 0.6 V.

The maximum storage temperature shall not exceed 200° C for packaged devices or 300° C for unassembled devices.

(3) Read the pattern after bake and perform endpoint electrical tests for table II herein for group C.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE A		5962-89527
		REVISION LEVEL A	SHEET 32

TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Interim electrical parameters (method 5004)	1, 7, 9
Final electrical test parameters (method 5004)	1*, 2, 3, 4, 5, 6, 7, 8a, 9, 10, 11
Group A test requirements (method 5005)	1*, 2, 3, 4, 5, 6, 7, 8a, 9, 10, 11
Groups C and D end-point electrical parameters (method 5005)	1, 2, 3

^{*} PDA applies to subgroup 1

- 4.4 <u>Programming procedures</u>. The programming procedures shall be as specified by the device manufacturer and shall be made available to the user on request.
- 4.5 <u>Erasing procedures</u>. The erasing procedures shall be as specified by the device manufacturer and shall be made available to the user on request.
- 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.
- 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
- 6.2 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.

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6.5 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444, or telephone (513) 296-5377.

6.6 Signal pin description

Pin name	Description					
RESET	Reset: This active low bidirectional control pin is used as an input to initialize the MCU to a known startup state and as an open-drain output to indicate that an internal failure has been detected in either the clock monitor or the computer operating properly (COP) circuit.					
XTAL, EXTAL	Crystal driver and external clock input: These pins provide the interface for either a crystal or a CMOS-compatible clock to control the internal clock generator circuitry. The frequency applied shall be four times higher than the desired clock rate.					
Е	E clock output: This for timing reference. t the XTAL and EXTA	The frequency o	output for the inte	ernally generated E clock which one fourth that of the input frec	n can be used quency a	
1RQ	Interrupt request: This pin provides the capability for asynchronously applying interrupts to the MCU. Either negative edge-sensitive or level-sensitive triggering is program selectable. This pin is configured to level-sensitive during reset. An external resistor connected V _{DD} is required on IRQ.					
X1RQ	Non-maskable interrupt: This pin provides the capability for asynchronously applying non-maskable interrupts to the MCU after a power on reset (POR). During reset, the X bit in the condition code register is set, and any interrupt is masked until enabled by software. This input is level-sensitive and requires an external pullup resistor to V _{DD} .					
MODA/L1R and MODB/V _{stby}	During reset, these pins are used to control the two basic operating modes and the two special operating modes. The LIR output can be used as an aid in debugging once reset is completed. The open-drain LIR pin goes to an active low during the first E-clock cycle of each instruction and remains low for the duration of that cycle. The Vstby (voltage standby) is used to retain RAM contents during device powerdown. The mode selections are shown below.					
	MODB MODA Mode selected					
	1 0 Single chip					
	1 1 Expanded multiplexed					
	0 0 Special bootstrap					
		0	1	Special test		
VRL, VRH	A/D converter reference voltages: These pins provide the reference voltage for the A/D converter.					
V _{SS}	GND					

6.7 <u>Approved source of supply</u>. An approved source of supply is listed in MIL-BUL-103. Additional sources will be added to MIL-BUL-103 as they become available. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

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STANDARDIZED MILITARY DRAWING SOURCE APPROVAL BULLETIN

DATE: 92-12-04

Approved sources of supply for SMD 5962-89527 are listed below for immediate acquisition only and shall be added to MIL-BUL-103 during the next revision. MIL-BUL-103 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DESC-EC. This bulletin is superseded by the next dated revision of MIL-BUL-103.

Standardized military drawing PIN	Vendor CAGE number	Vendor similar PIN <u>1</u> /
5962-8952701XX	04713	68HC811E2/BXAJC
5962-8952701YX	04713	68HC811E2/BYCJC

<u>1</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE
numberVendor name
and address

04713 Motorola Semiconductor

5005 E. McDowell Road Phoenix, AZ 85008

Point of contact: 2100 E. Elliot Road

Tempe, AZ 84284

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in this information bulletin.